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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Wendell P. Noble et al.

Title: ULTRA HIGH DENSITY FLASH MEMORY

Docket No.: 303.330US3

Serial No.: 09/866,938

Filed: May 29, 2001

Due Date: N/A

Examiner: Jack Chen

Group Art Unit: 2813

Commissioner for Patents
Washington, D.C. 20231

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We are transmitting herewith the following attached items (as indicated with an "X"):

- ☒ A return postcard.
- ☒ A Supplemental Information Disclosure Statement (1 pg.), Form 1449 (6 pgs.), and copies of 120 cited references.
- ☒ A Communication Concerning Co-Pending Applications (3 pgs.).

Please consider this a **PETITION FOR EXTENSION OF TIME** for sufficient number of months to enter these papers and please charge any additional required fees or credit overpayment to Deposit Account No. 19-0743.

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.
P.O. Box 2938, Minneapolis, MN 55402 (612-373-6900)

By: *Raymond R. Berdie*
Atty: Raymond R. Berdie
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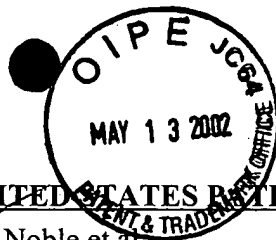
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SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.
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S/N 09/866,938



PATENT

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SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

In compliance with the duty imposed by 37 C.F.R. § 1.56, and in accordance with 37 C.F.R. §§ 1.97 *et. seq.*, the enclosed materials are brought to the attention of the Examiner for consideration in connection with the above-identified patent application. Applicants respectfully request that this Supplemental Information Disclosure Statement be entered and the documents listed on the attached Form 1449 be considered by the Examiner and made of record. Pursuant to the provisions of MPEP 609, Applicants request that a copy of the 1449 form, initialed as being considered by the Examiner, be returned to the Applicants with the next official communication.

Pursuant to 37 C.F.R. §1.97(b), it is believed that no fee or statement is required with the Supplemental Information Disclosure Statement. However, if an Office Action on the merits has been mailed, the Commissioner is hereby authorized to charge the required fees to Account No. 19-0743 in order to have this Supplemental Information Disclosure Statement considered.

The Examiner is invited to contact the Applicants' Representative at the below-listed telephone number if there are any questions regarding this communication.

Respectfully submitted,

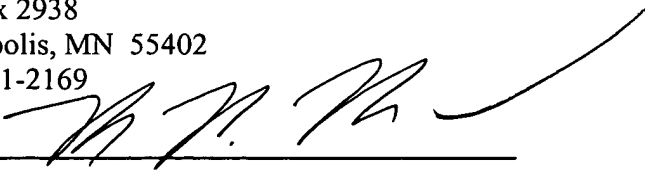
WENDELL P. NOBLE ET AL.

By their Representatives,

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Date 5-7-2002

By

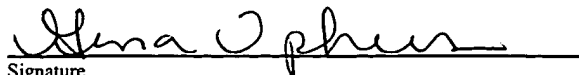

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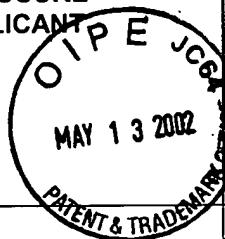


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**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

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Complete if Known

Application Number	09/866938
Filing Date	May 29, 2001
First Named Inventor	Noble Jr., Wendell
Group Art Unit	2813
Examiner Name	Chen, Jack

Sheet 1 of 6

Attorney Docket No: 00303.330US3

US PATENT DOCUMENTS

Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
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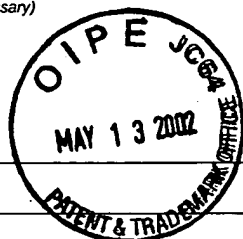
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Group Art Unit	2813
Examiner Name	Chen, Jack

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OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
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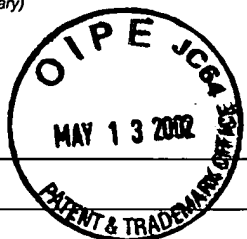
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Sheet 3 of 6

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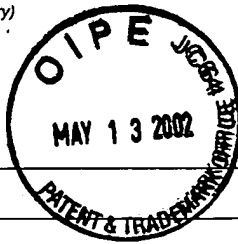
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Group Art Unit	2813
Examiner Name	Chen, Jack

Sheet 4 of 6

Attorney Docket No: 00303.330US3

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
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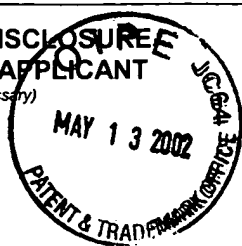
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Application Number	09/866938
Filing Date	May 29, 2001
First Named Inventor	Noble Jr., Wendell
Group Art Unit	2813
Examiner Name	Chen, Jack

Sheet 6 of 6

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OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
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